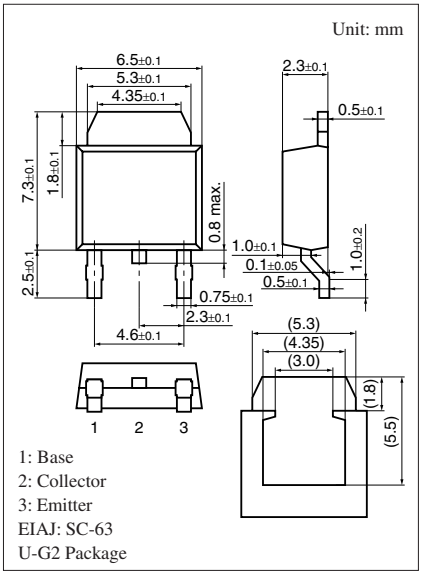
2SD2453

Silicon NPN triple diffusion planar type

For high current transfer ratio and power amplification

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$



Note) Self-supported type package is also prepared.

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)		V_{CBO}	80	V
Collector-emitter voltage (Base open)		V_{CEO}	60	V
Emitter-base voltage (Collector open)		V_{EBO}	6	V
Collector current		I_C	2	A
Peak collector current *		I_{CP}	4	A
Base current		I_B	1	A
Collector power dissipation	$T_C = 25°C$	P_C	10	W
			1	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

Note) Non-repetitive peak collector current

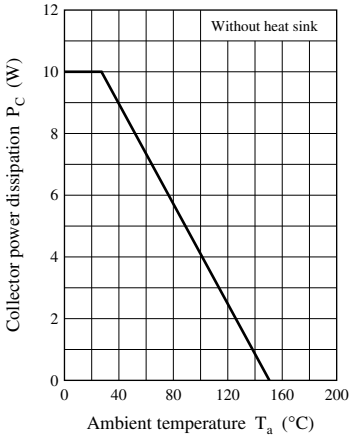
■ Electrical Characteristics $T_a = 25°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 25$ mA, $I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 80$ V, $I_E = 0$			100	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 40$ V, $I_B = 0$			100	μA
Emiter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6$ V, $I_C = 0$			100	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 4$ V, $I_C = 0.5$ A	500		2 500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2$ A, $I_B = 0.05$ A			1	V
Transition frequency	f_T	$V_{CE} = 12$ V, $I_C = 0.2$ A, f = 10 MHz		50		MHz

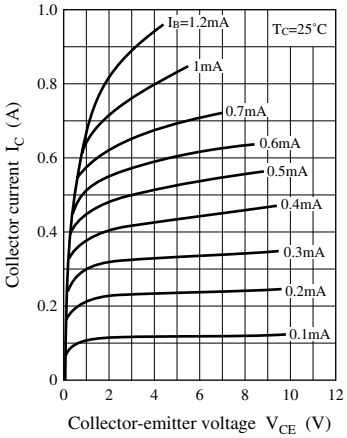
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. ∗: Rank classification

Rank	Q	R	S
h_{FE}	500 to 1 000	800 to 1 500	1 200 to 2 500

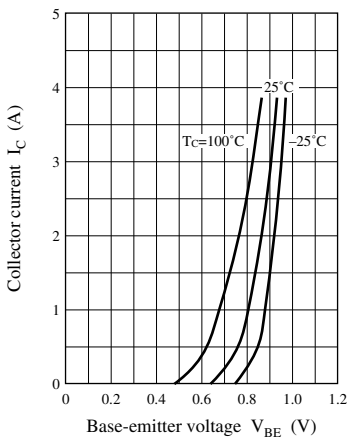
P_C — T_a



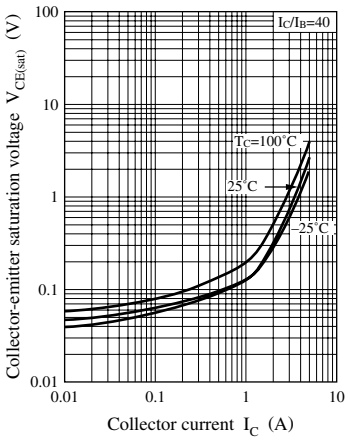
I_C — V_{CE}



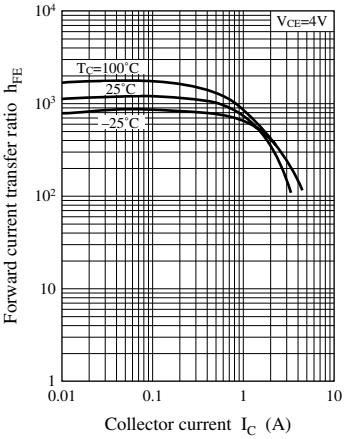
I_C — V_{BE}



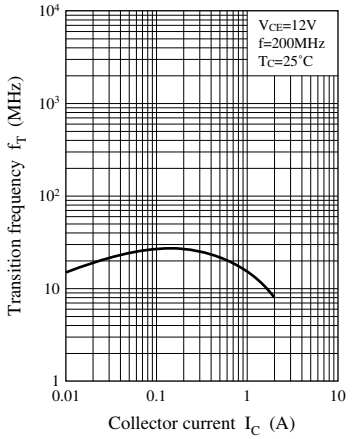
$V_{CE(sat)}$ — I_C



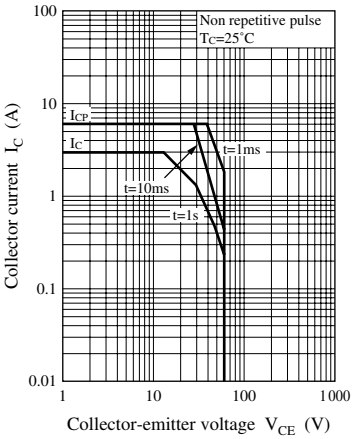
h_{FE} — I_C



f_T — I_C



Safe operation area



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